**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO-220 plastic package.

### 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- Low forward conduction voltage
- · Negligible switching losses

## 3. Applications

- · DC to DC converters
- Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	100	V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 134 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	15	А
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; both diodes conducting	-	-	30	А
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.48	0.55	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.41	0.48	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.56	0.63	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.53	0.6	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.64	0.71	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.6	0.67	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode	-	-	50	μA
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode	-	-	30	mA

# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1   A2
2	K	cathode		
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode	TO-220E	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNS30H100C	TO220	WNS30H100CQ	Tube	50	TO220E	26-April-2019

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## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_{RWM}$	limiting crest working reverse voltage		-	100	V
$V_R$	limiting reverse voltage	DC	-	100	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 134 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	-	15	А
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; both diodes conducting	-	30	А
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	330	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	363	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

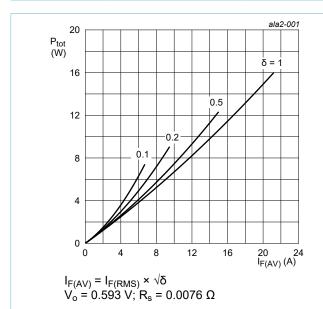


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

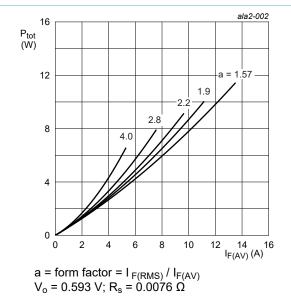


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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### **Dual power Schottky diode**

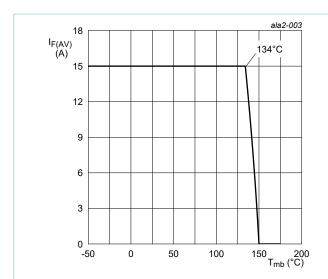


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

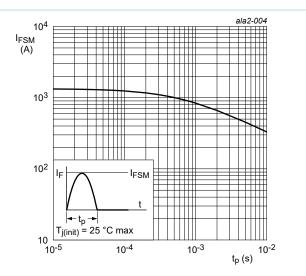


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

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**Dual power Schottky diode** 

### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	per diode; Fig. 5	-	-	1.3	K/W
	from junction to mounting base	both diodes conducting	-	-	0.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

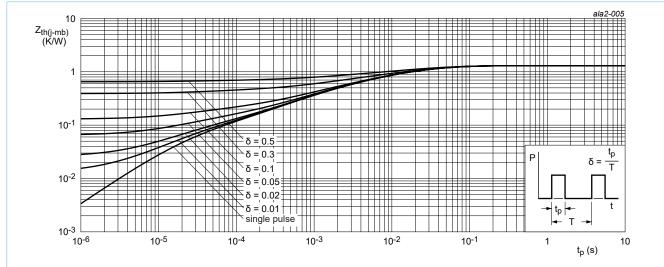


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

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### 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics		,		,	
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.48	0.55	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.41	0.48	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	-	0.56	0.63	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	-	0.53	0.6	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u> ; per diode	_	0.64	0.71	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u> ; per diode	_	0.6	0.67	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; Fig. 7; Fig. 8; per diode}$	-	-	50	μΑ
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> ; per diode	-	-	30	mA

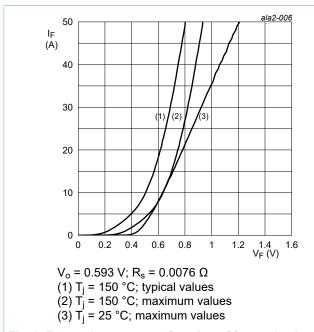


Fig. 6. Forward current as a function of forward voltage; per diode

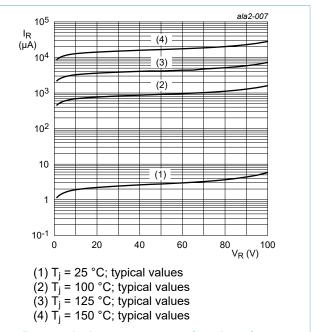
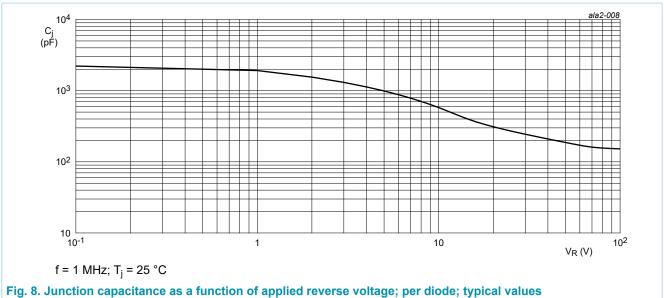


Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

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### **Dual power Schottky diode**



## 10. Package outline

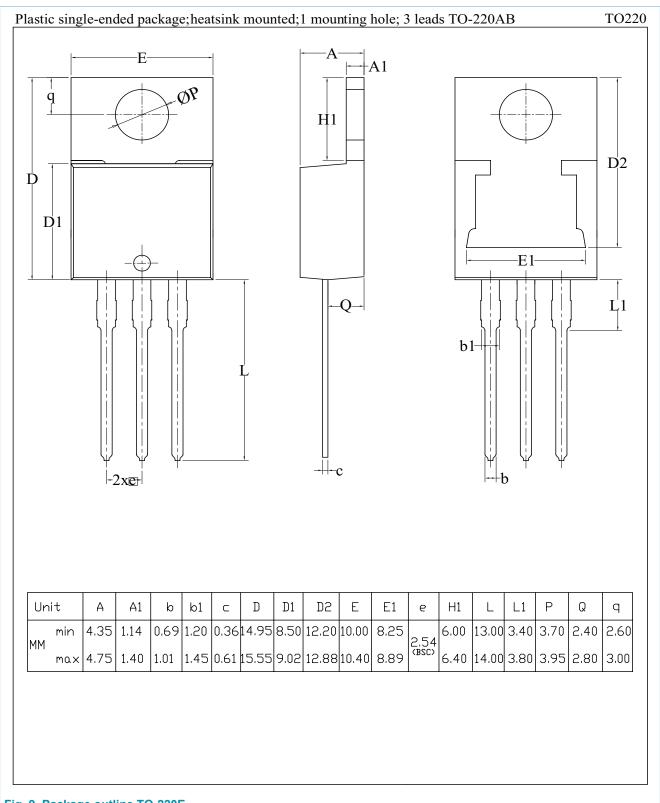


Fig. 9. Package outline TO-220E

## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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## **WNS30H100C**

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